PMPB12UN

20 V single N-channel Trench MOSFET

6 July 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- · Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	11.3	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_{D} = 7.9 A; T_{j} = 25 °C		-	14	18	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain	1 6	D	
2	D	drain	7 5		
3	G	gate		G TI A	
4	S	source	3 8 4	\$ 017aaa253	
5	D	drain	Transparent top view	Transparent top view	077444256
6	D	drain	DFN2020MD-6 (SOT1220)		
7	D	drain			
8	S	source			

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB12UN	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB12UN	1F

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	11.3	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7.9	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	31	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T _{amb} = 25 °C	[1]	-	1.8	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

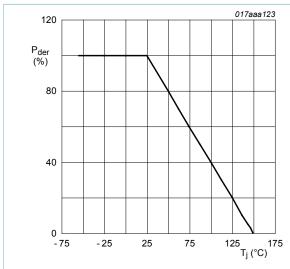


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

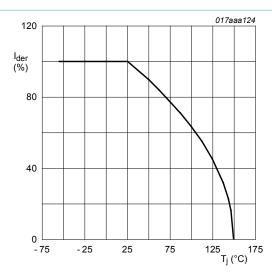


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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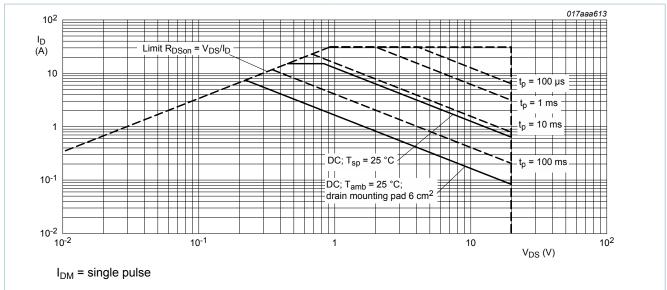


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
and a)	thermal resistance		[1]	-	235	270	K/W
	from junction to		<u>[2]</u>	-	67	74	K/W
	ambient		[3]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s

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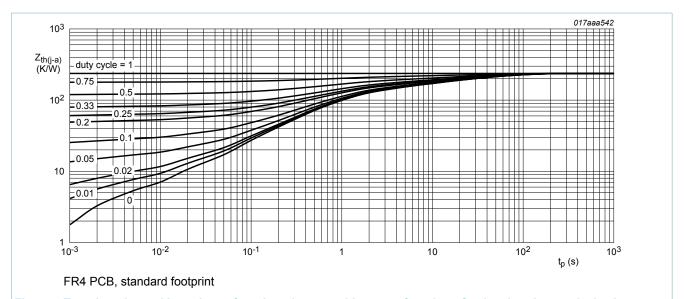


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

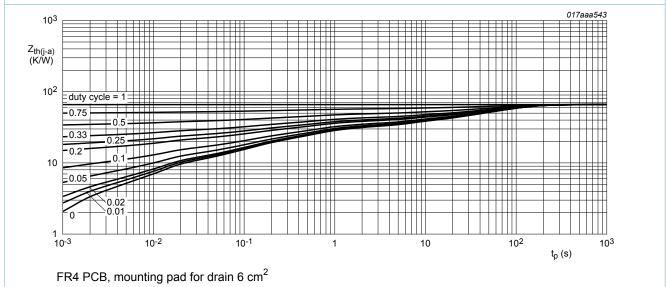


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C	0.4	0.7	1	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 7.9 A; T _j = 25 °C	-	14	18	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 7.9 A; T _j = 150 °C	-	21	27	mΩ
		V _{GS} = 2.5 V; I _D = 3.5 A; T _j = 25 °C	-	17	23	mΩ
		V _{GS} = 1.8 V; I _D = 3.5 A; T _j = 25 °C	-	21	33	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7.9 A; T _j = 25 °C	-	25	-	S
R_G	gate resistance	f = 1 MHz	-	1.4	-	Ω
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 6 A; V_{GS} = 4.5 V; T_{j} = 25 °C	-	8.8	13	nC
Q_{GS}	gate-source charge		-	1	-	nC
Q_{GD}	gate-drain charge		-	2.2	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	886	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	233	-	pF
C _{rss}	reverse transfer capacitance		-	129	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I_{D} = 6 A; V_{GS} = 4.5 V;	-	9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	20	-	ns
t _{d(off)}	turn-off delay time		-	26	-	ns
t _f	fall time		-	26	-	ns
Source-dra	in diode		1		'	
V_{SD}	source-drain voltage	I _S = 1.8 A; V _{GS} = 0 V; T _j = 25 °C	-	0.6	1.2	V

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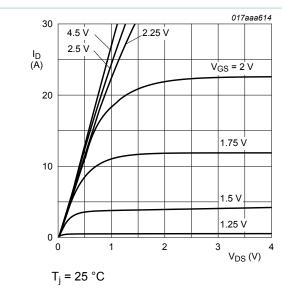


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

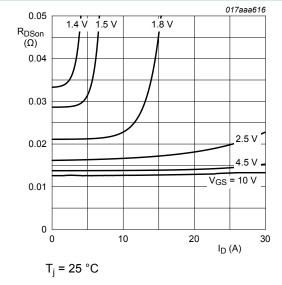


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

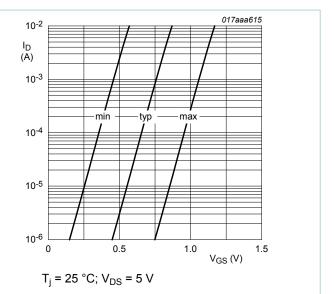
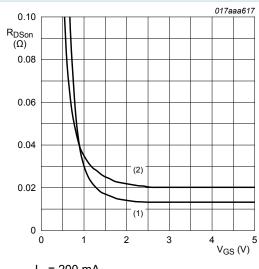


Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 200 \text{ mA}$ (1) $T_j = 150 \text{ °C}$ (2) $T_i = 25 \text{ °C}$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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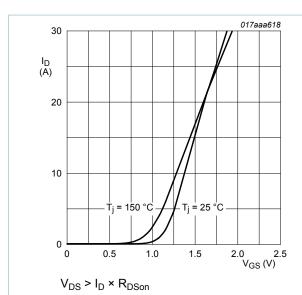


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

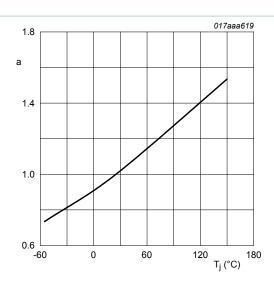


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

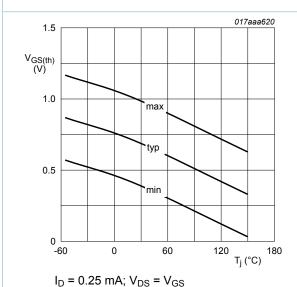
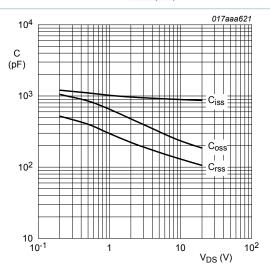


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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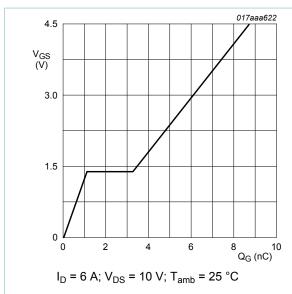


Fig. 14. Gate-source voltage as a function of gate charge; typical values

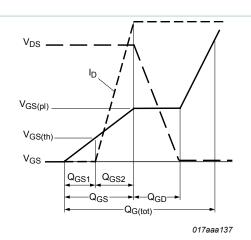


Fig. 15. Gate charge waveform definitions

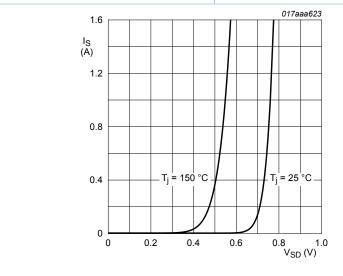
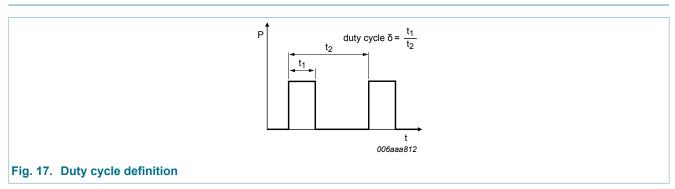


Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

 $V_{GS} = 0 V$



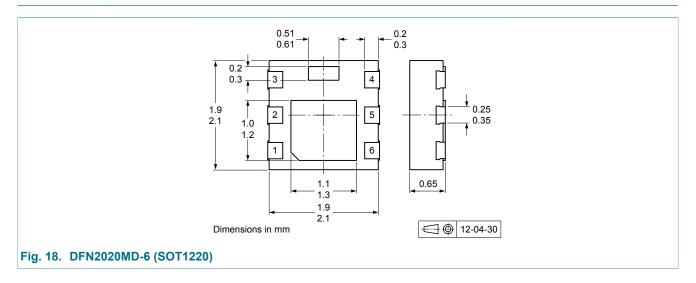
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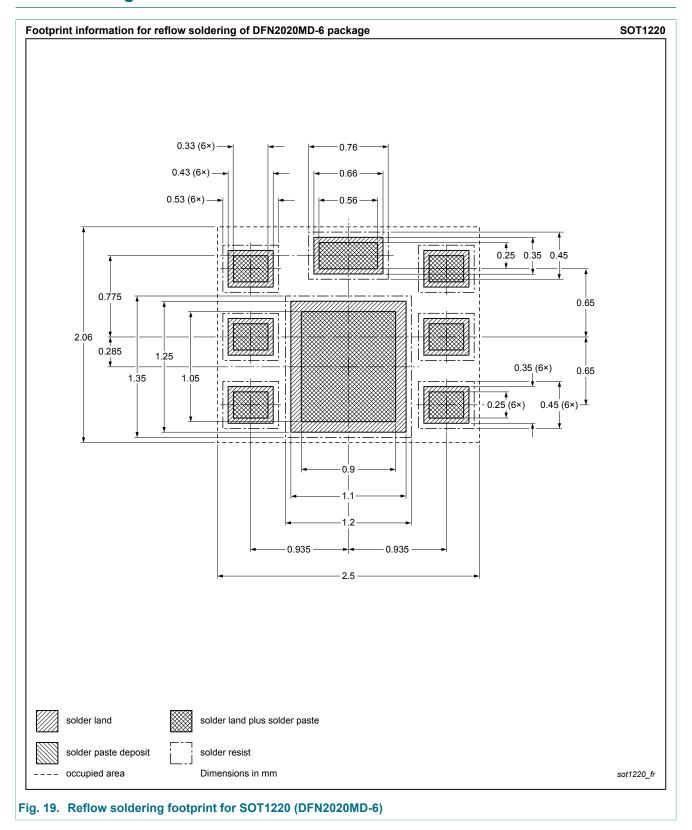
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9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB12UN v.1	20120706	Product data sheet	-	-

20 V single N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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